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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Jack O. Chu, et al.

Docket: 16315

Patent No.: 6,750,119B2

Dated: October 26, 2004

Issued: June 15, 2004

For: EPITAXIAL AND POLYCRYSTALLINE  
GROWTH OF  $Si_{1-x}yGe_xC_y$  AND  $Si_{1-y}C_y$   
ALLOY LAYERS ON SI BY UHV-CVD

Certificate  
NOV 02 2004  
of Correction

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REQUEST FOR CERTIFICATE OF CORRECTION**

Sir:

It appears that errors have been introduced in the course of printing the Patent issued in the above application, it is respectfully requested that the Commissioner issue a Certificate of Correction in the following respects:

On the Title Page, item (56), insert the following:

-- 2002/0016085      2/2002      Huang, et al. .... 438/798  
6306211      10/2001      Takahashi, et al. .... 117/86 -- See attached

Notice of References Cited.

Respectfully submitted,

Leslie S. Szivos  
Reg. No. 39, 394

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**CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on October 26, 2004.

Dated: October 26, 2004

Leslie S. Szivos

NOV 04 2004

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,750,119 *B2*  
DATED : June 15, 2004  
INVENTOR(S) : Jack O. Cu, et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

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MAILING ADDRESS OF SENDER:

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PATENT NO. 6,750,119

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UNITED STATES PATENT AND TRADEMARK OFFICE  
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PATENT NO. 6,750,119

*NO. 0 4 2004*

<b>Notice of References Cited</b> 	Application/Control No. <b>09/838,892</b>	Applicant(s)/Patent Under Reexam <b>Chu et al</b>	
	Examiner <b>Savitri Mulpuri</b>	Art Unit <b>2812</b>	Page 1 of 1

### U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>	
A	6,190,975	2/01	Kubo et al	438	285
B	2001/0160605	10/02	Kanazawa et al	438	689
C	5,683,934	11/97	Candelaria et al	438	----
D	2002/0016095	2/2002	HUANG et al	438	798
E	6 306211	10/2001	TAKAHASHI et al	437	86
F					
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### FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Country	Name	Classification <sup>2</sup>	
N						
O						
P						
Q						
R						
S						
T						

### NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Todd et al, "growth of heteroeptitaxial SiGeC alloys on silicon using novel chemsitry., Appl. Physc. letts 67 9() 28august 1995
V	
W	
X	

\* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

<sup>1</sup> Dates in MM-YYYY format are publication dates.

<sup>2</sup> Classifications may be U.S. or foreign.